

**METHOD FOR MANUFACTURING DEVICE SUBSTRATE  
WITH METAL BACK-GATE AND STRUCTURE FORMED THEREBY**

**ABSTRACT OF THE DISCLOSURE**

A method (and resultant structure) of forming a semiconductor device, includes  
5 forming a metal-back-gate over a substrate and a metal back-gate, forming a passivation  
layer on the metal back-gate to prevent the metal back-gate from reacting with radical  
species, and providing an intermediate gluing layer between the substrate and the metal  
back-gate to enhance adhesion.